Supporting Information

Investigating the Formation of MoSe₂ and TiSe₂ Films from Artificially Layered Precursors.

Aaron M. Miller, Danielle M. Hamann, Erik C. Hadland, David C. Johnson*



Figure S1. XRR of Ti|Se annealing study showing evolution of film thickness and roughness as energy is applied to the system.



Figure S2. Specular (a.) and in-plane (b.) XRD patterns for additional Ti|Se precursors annealed at 350°C showing the influence of precursor composition on structure.



Figure S3. XRR patterns for various Ti|Se precursors annealed at 350 °C showing the variation in roughness and loss of layers as a function of stoichiometry.



Figure S4. Experimental (red) and simulated (black) XRR patterns demonstrating effect of oxide growth. Based on the amount of excess material in each film, the annealed films developed either a thin (~9 Å) or thick (~60 Å) oxide layer.